

# SELECTIVE SALICIDATION METHODS

## Abstract

Methods for selective salicidation of a semiconductor device. The invention implements a chemical surface pretreatment by immersion in ozonated water  $H_2O$  prior to metal deposition. The pretreatment forms an interfacial layer that prevents salicidation over an n-type structure. As a result, the invention does not add any additional process steps to the conventional salicidation processing.